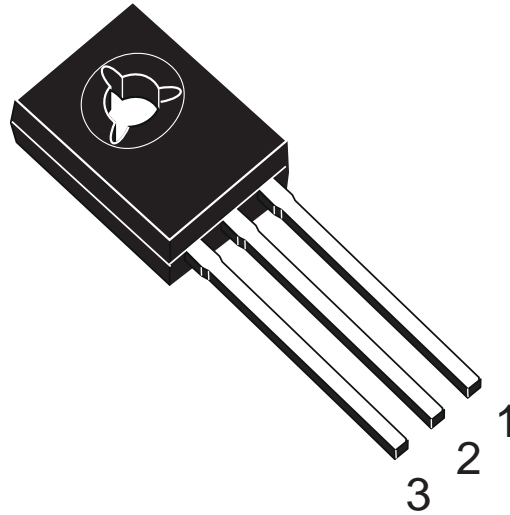


工业型号	公司型号	封装形式	通俗命名	包装规格
2SD882	HD882	TO-126	882	每袋1000Pcs (1K), 每盒10000Pcs (10K)

2SD882 Series Pin Assignment



3-Lead Plastic TO-126, Package Code: T

1: E (Emitter-发射极), 2: C (Collector-集电极), 3: B (Base-基极)

2SD882
PNP EPITAXIAL SILICON TRANSISTOR
MEDIUM POWER LOW VOLTAGE TRANSISTOR

DESCRIPTION

The 2SD882 is a medium power low voltage transistor, designed for audio power amplifier, DC-DC converter and voltage regulator.

FEATURES

- *High current output up to 3A
- *Low saturation voltage
- *Complement to 2SB772

产品特征

低饱和压降
高电流容量
与2SB772配对使用

应用领域

常规开关、电压调整
继电器驱动、DC-DC变换器
直流之间转换、音频功率放大器

■ 极限参数 (Ta=25°C, unless otherwise specified)

符号	参数说明	数值	单位
V _{CBO}	集电极~基极电压	60	V
V _{CEO}	集电极~发射极直流电压	30	
V _{EBO}	发射极~基极直流电压	6	
I _B	Base Current	1	A
I _C	集电极最大直流电流	3	
P _C	耗散功率 (T _C =25°C)	12	W
T _j	结温	150	°C
T _{stg}	贮存温度	-55~+150	

电参数 (T_A=25°C, unless otherwise specified)

符号	参数说明	测试条件	最小值	典型值	最大值	单位
V _{(BR)CEO}	集电极~发射极直流电压	I _C =10mA, I _B =0	30	45	--	V
V _{(BR)CBO}	集电极~基极电压	I _C =1mA, I _B =0	60	80	--	
V _{(BR)EBO}	发射极~基极直流电压	I _E =1mA, I _C =0	6	9	--	
V _{cesat}	集电极~发射极饱和电压	I _C =3A, I _B =0.3A	--	0.5	1.0	
V _{besat}	发射极~基极饱和电压	I _C =3A, I _B =0.3A	--	--	1.2	
I _{CBO}	集电极~基极反向电流	V _{CB} =40V, I _E =0	--	--	100	
I _{CEO}	集电极~发射极反向电流	V _{CE} =30V, I _B =0	--	--	100	
I _{EBO}	发射极~基极反向电流	V _{EB} =6V, I _C =0	--	--	100	
f _T	特征频率	V _{CE} =10V, I _C =0.1A	--	80	--	MHz
R _{th(j-c)}	结到管壳的热阻		--	--	10	°C/W
h _{FE} ①	集直流电流放大系数	V _{CE} =5V, I _C =100mA	100	250	--	
h _{FE} ②		V _{CE} =5V, I _C =1A	80	--	--	

■ 特征曲线

Fig-1: Reverse Biased Safe Operating Area

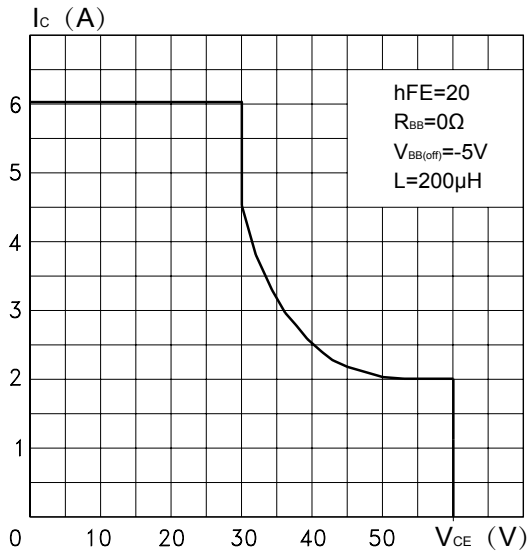


Fig-2: DC Current Gain

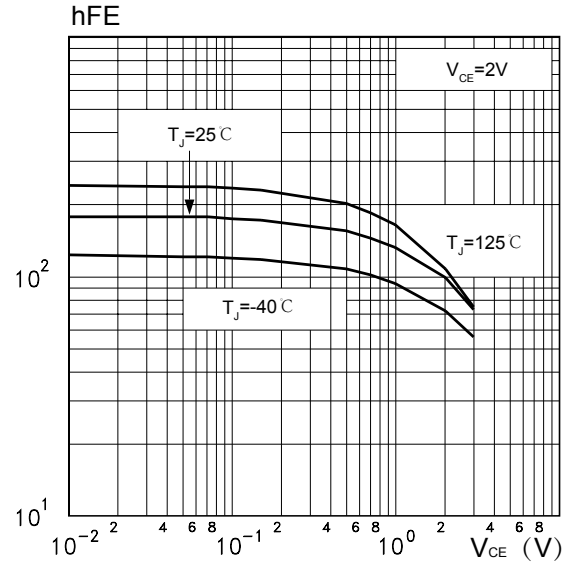


Fig-3: Collector-emitter Saturation Voltage

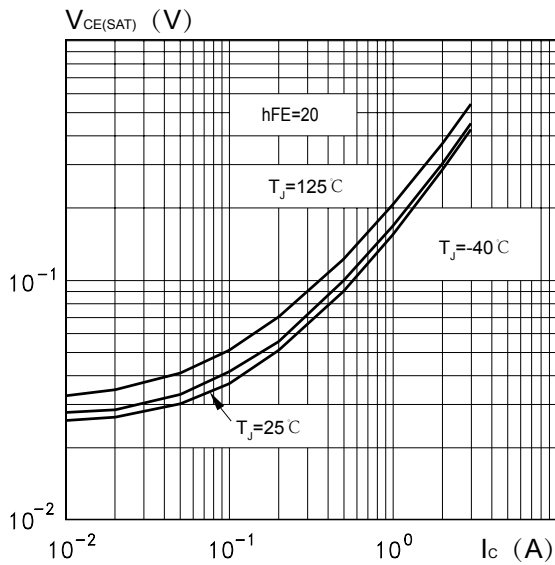
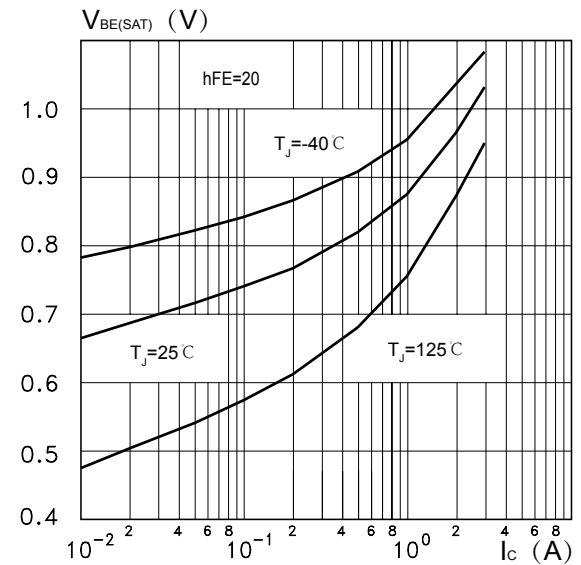
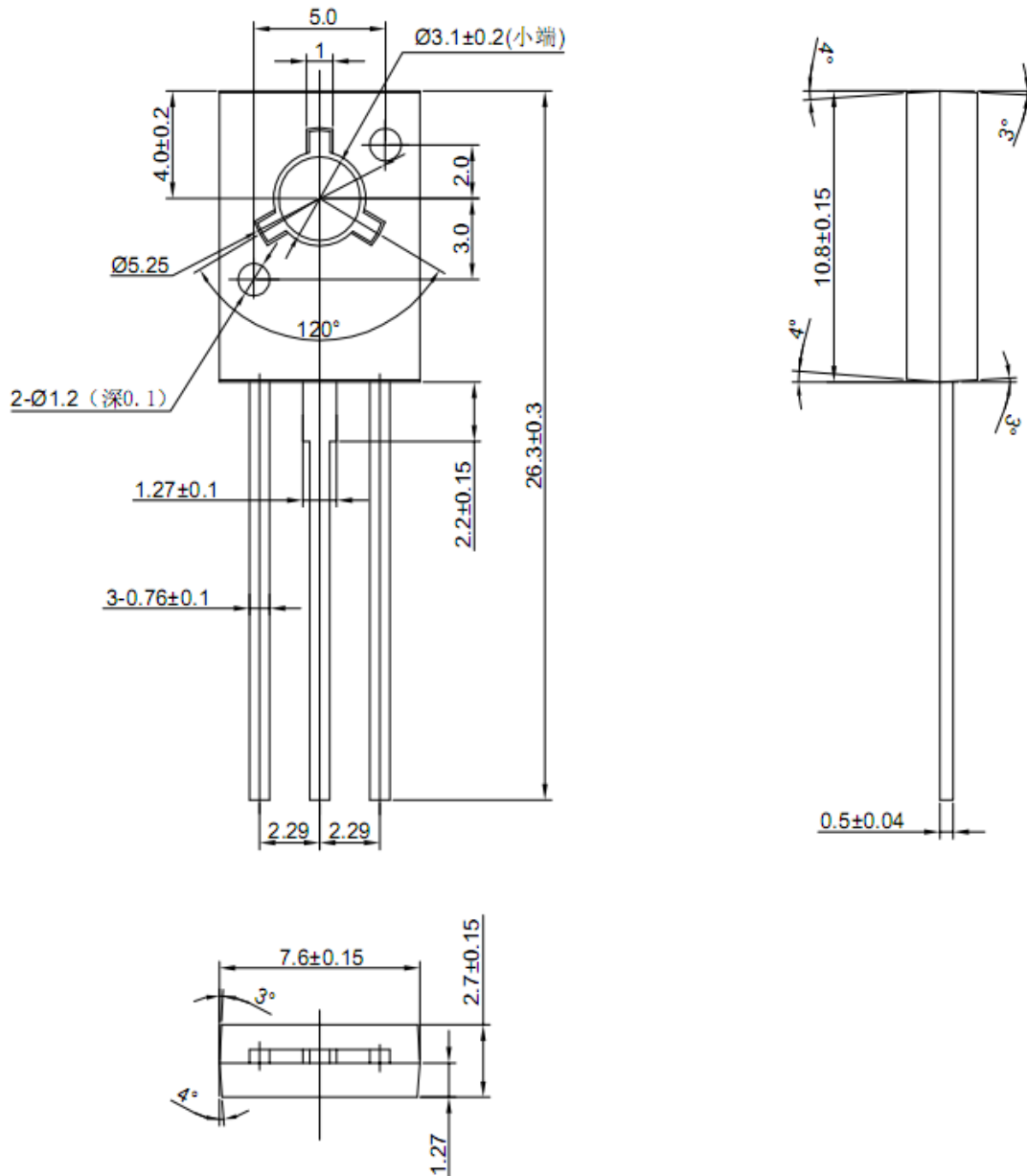


Fig-4: Base-emitter Saturation Voltage



PACKAGE DIMENSIONS (UNIT: mm)



Manufacturers version information

2007-03-11, HAOHAI™ Product Data-S1.0
2010-04-10, HAOHAI™ Product Data-S1.1
2014-07-11, HAOHAI™ Product Data-S2.0
2018-10-23, HAOHAI™ Product Data-S2.1
2021-08-30, HAOHAI™ Product Data-S2.2



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